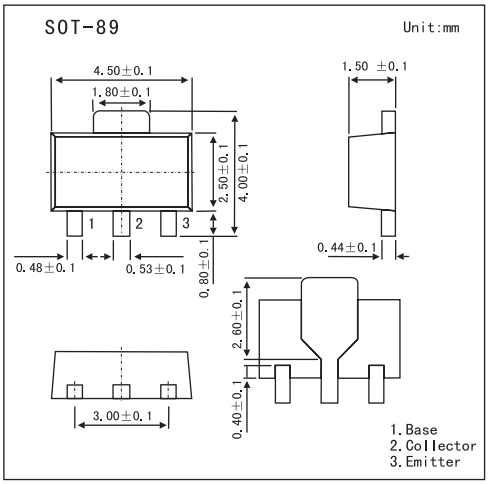
TY Semicondutor®

Product specification

KSC2881



■ Features

- Collector-Emitter Voltage : V_{CEO}=120V
- Current Gain Bandwidth Productor : f_T=120MHz
- Collector Dissipation : P_C=1 to 2W in Mounted on Ceramic Board

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Base Current	I_B	160	mA
Collector Power Dissipation	P_C	500	mW
	P_C*	1,000	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55 to +150	℃

* Mounted on Ceramic Board (250mm^{2}X0.8mm)

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=10μA, I_B=0	120			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=1mA, I_C=0	5			V
Collector Cut-off Current	I_{CBO}	V_{CB}=120V, I_E=0			100	nA
Emitter Cut-off Current	I_{EBO}	V_{BE}=5V, I_C=0			100	nA
DC Current Gain	h_{FE}	V_{CE}=5V, I_C=100mA	80		240	
Collector-Emitter Saturation Voltage	$V_{CE\ (sat)}$	I_C=500mA, I_B=50mA			1.0	V
Base-Emitter On Voltage	$V_{BE\ (on)}$	V_{CE}=5V, I_C=500mA			1.0	V
Current Gain Bandwidth Product	f_T	V_{CE}=5V, I_C=100mA		120		MHz
Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz			30	pF

■ h_{FE} Classification

Marking	SCO	SCY
Rank	O	Y
Type	80～160	120～240